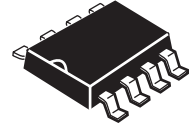
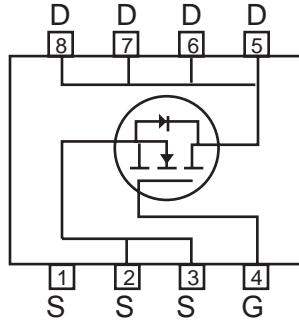


N-Channel Enhancement Mode MOSFET

Features

- 20V/6.0A
 $R_{DS(ON)}=40m.$ (Typ.) @ $V_{GS}=4.5V, I_D=6A$
 $R_{DS(ON)}=45m.$ (Typ.) @ $V_{GS}=2.5V, I_D=5.2A$
- Super High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged
- SOP-8 Package

Pin Description



Top View of SOP-8

Applications

- Power Management in Notebook Computer
 Portable Equipment and Battery Powered Systems.

Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Test Condition	NK9410			Unit
			Min.	Typ.	Max.	
Static						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	16			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=12V, V_{GS}=0V$			1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	0.4		1.3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 8V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=4.5V, I_{DS}=6A$		40	50	m Ω
		$V_{GS}=2.5V, I_{DS}=5.2A$		45	55	
V_{SD}	Diode Forward Voltage	$I_{SD}=1.5A, V_{GS}=0V$			1.2	V

Absolute Maximum Ratings ($T_A = 25$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 8	
I_D^*	Maximum Drain Current – Continuous	6	A
I_{DM}	Maximum Drain Current – Pulsed	20	

* Surface Mounted on FR4 Board, $t \leq 10$ sec.